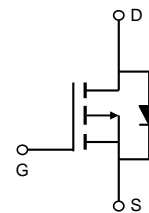


General Description

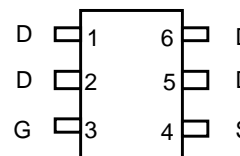
The AO6401A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V.

This device is suitable for use as a load switch or in PWM applications.



Product Summary

- $V_{DS} (V) = -30V$
- $I_D = -5A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 47m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 64m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 85m\Omega$ ($V_{GS} = -2.5V$)



SOT23-6

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted			
Parameter		Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^\circ C$	I_D	A
Pulsed Drain Current ^C		I_{DM}	-28
Power Dissipation ^B	$T_A=25^\circ C$	P_D	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$t \leq 10s$	$R_{\theta JA}$	47.5	62.5	$^\circ C/W$
Maximum Junction-to-Ambient	Steady-State		74	110	$^\circ C/W$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	37	50	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}, V_{GS}=0\text{V}$			-1	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.5	-0.9	-1.3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	-28			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-5\text{A}$		39	47	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-4\text{A}$		45	64	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-1\text{A}$		59	85	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-5\text{A}$		18		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		645	780	pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			55	80	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	4	7.8	12	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-5\text{A}$		14	17	nC
$Q_g(4.5\text{V})$	Total Gate Charge			7	8.5	nC
Q_{gs}	Gate Source Charge			1.5		nC
Q_{gd}	Gate Drain Charge			2.5		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=3\Omega, R_{GEN}=3\Omega$		6.5		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off DelayTime			41		ns
t_f	Turn-Off Fall Time			9		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		11	13.5	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		3.5		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

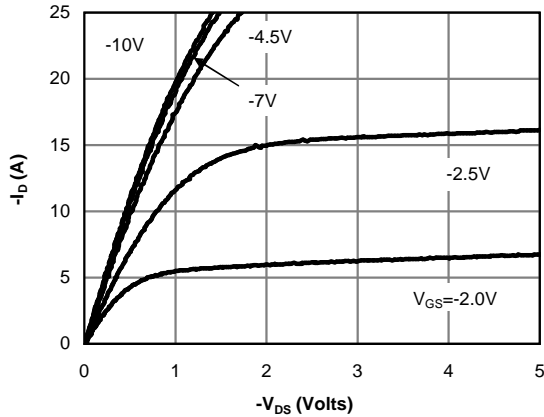


Figure 1: On-Region Characteristics (Note E)

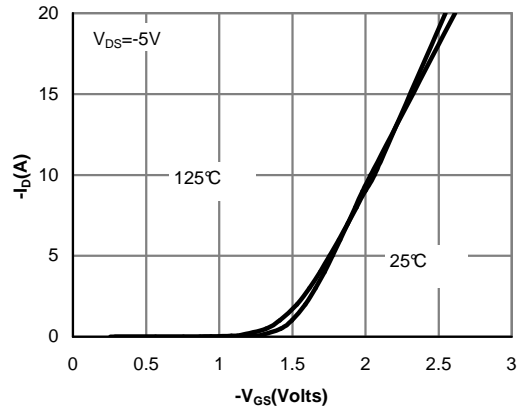


Figure 2: Transfer Characteristics (Note E)

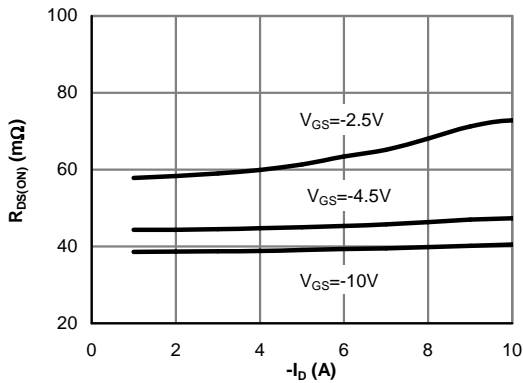


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

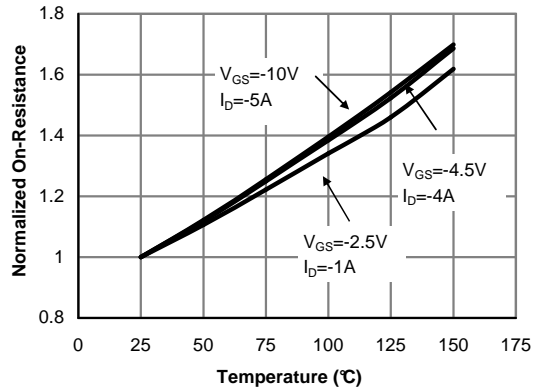


Figure 4: On-Resistance vs. Junction Temperature (Note E)

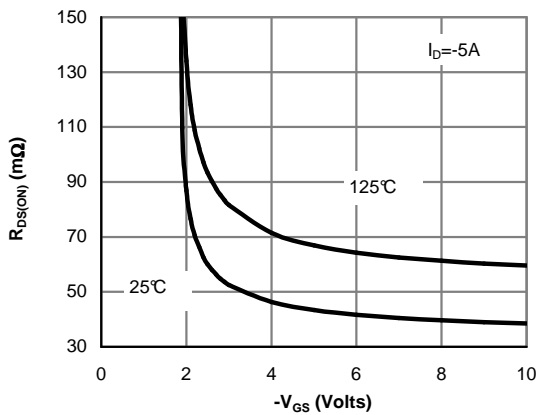


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

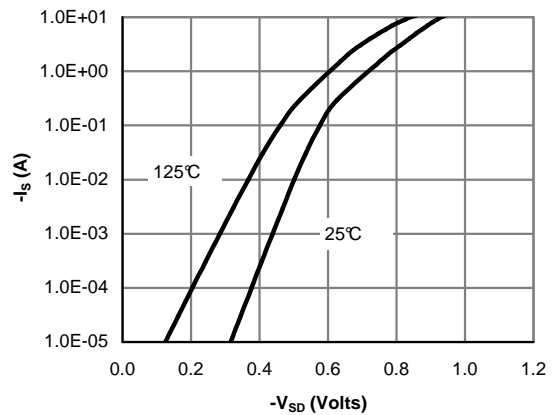


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

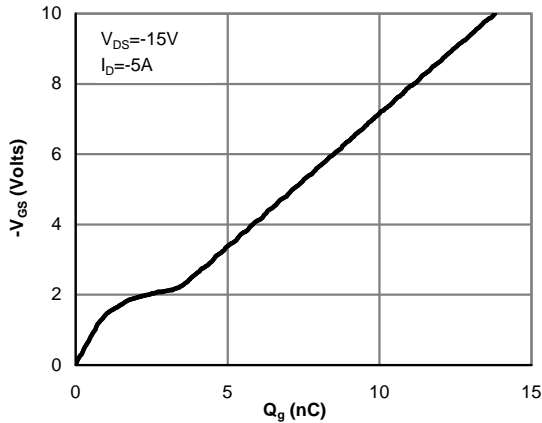


Figure 7: Gate-Charge Characteristics

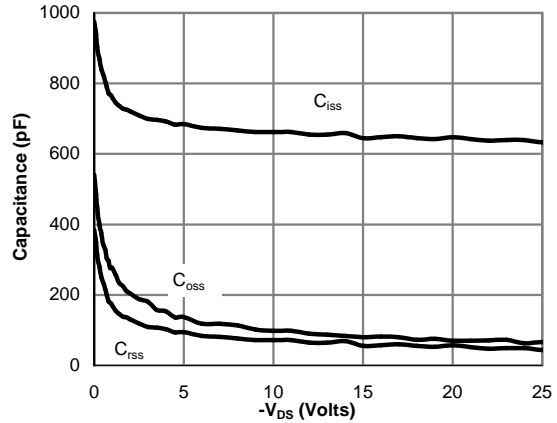


Figure 8: Capacitance Characteristics

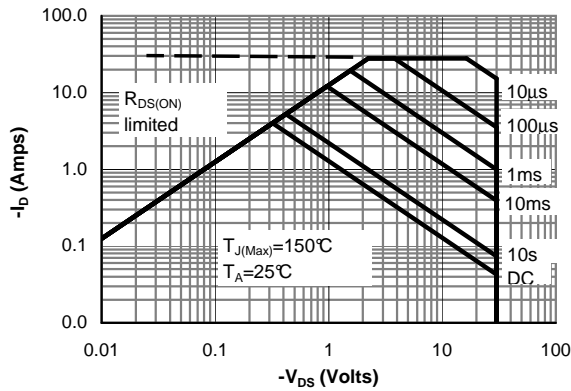


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

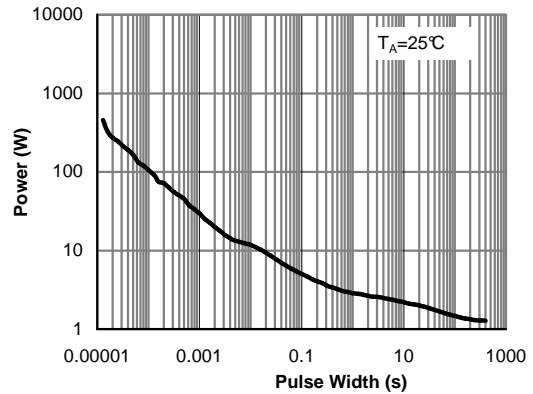


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

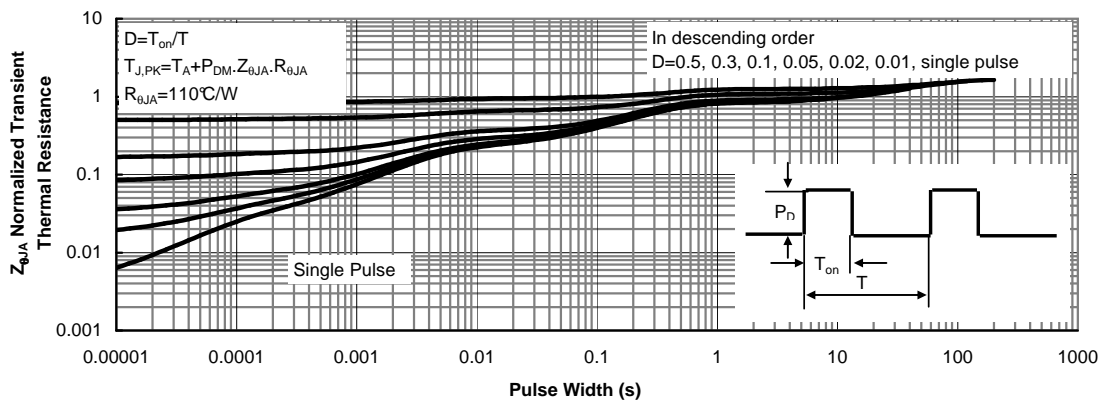
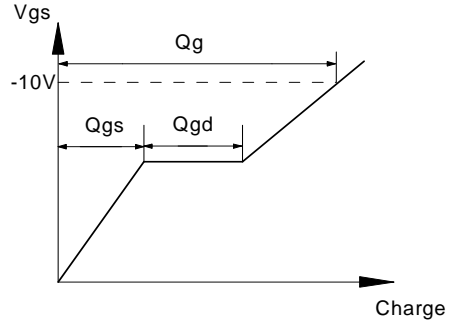
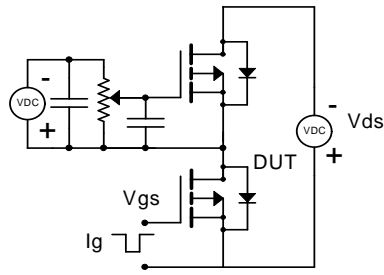


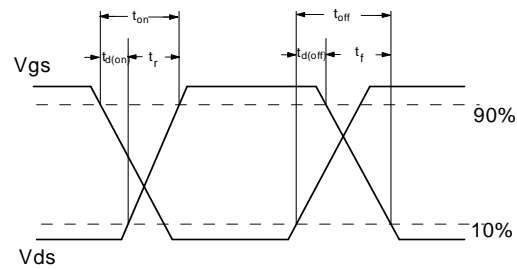
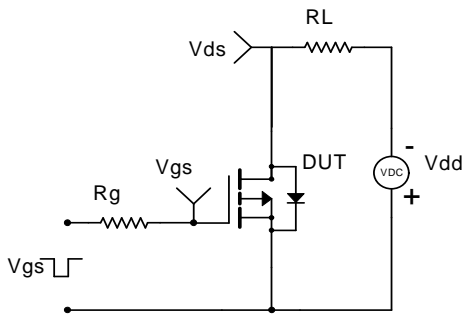
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform

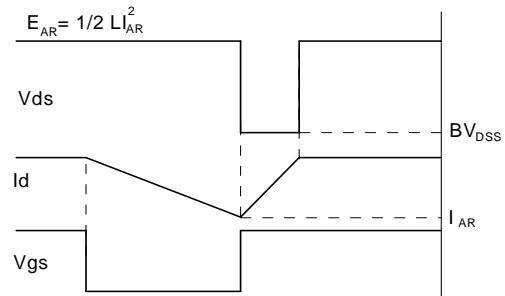
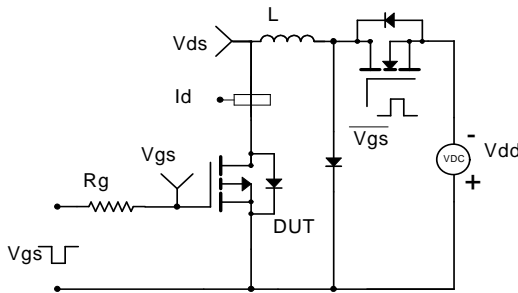
30V P-Channel MOSFET



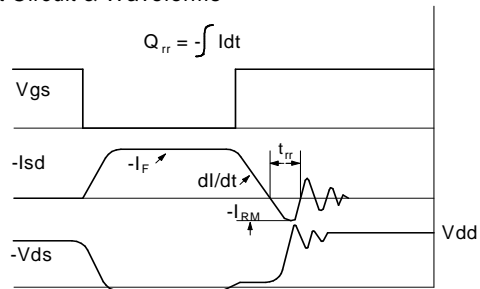
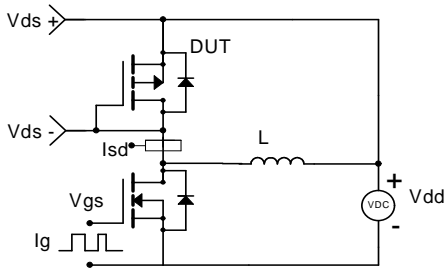
Resistive Switching Test Circuit & Waveforms



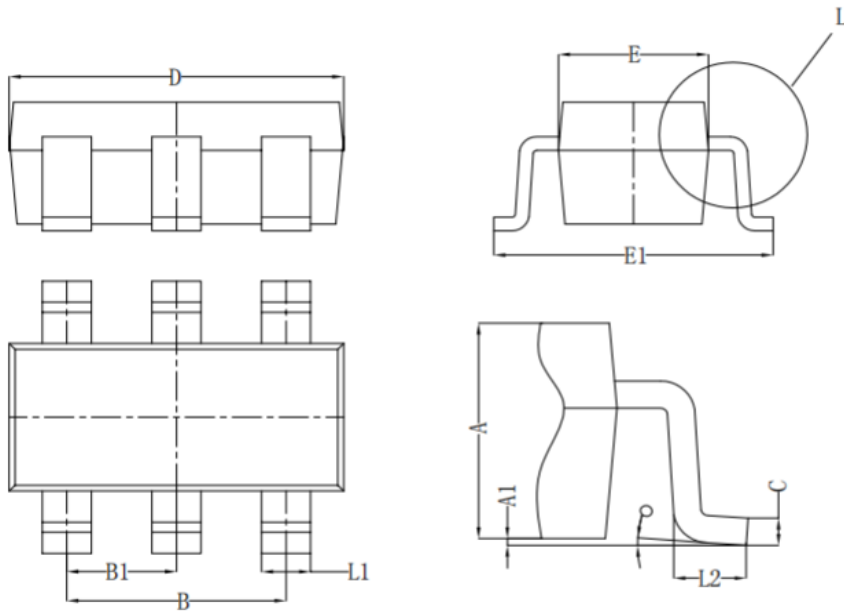
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

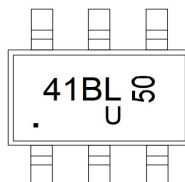


SOT23-6 PACKAGE OUTLIE DIMENSIONS



Symbol	Dim in mm		
	Min	Nor	Max
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.300	0.450	0.600
o	0°	4°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW AO6401A	SOT23-6	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)